

UMZ-T2-397-016-G

VOLTAGE CONTROLLED OSCILLATOR WITH INTERNAL DOUBLER

Package: 016, 12.7mm x 12.7mm x 5.59mm



Features

- Internal Frequency Doubler and Buffer AMP
- 1/2 Frequency Output Provided
- Frequency: 6525MHz
- Resonator: Microstrip
- PCB: Rogers
- Package Size: 12.7mm x 12.7mm x 5.59mm (0.5in x 0.5in x 0.22in)

Applications

- DRO Replacements
- Higher Frequency Applications
- Wide Bandwidth Applications
- Test Instrumentation

V_{TUNE} V_{TUNE} V_{TUNE} V_{TUNE} Resonator V_{Circuit} Resonator V_{Circuit} V_{Circuit}

Functional Block Diagram

Product Description

This series of VCO modules offers ultra-linear tuning across their specified frequency band.

Ordering Information

UMZ-T2-397-016-G Contact us at 1-480-756-6070

Optimum Technology Matching® Applied

GaAs HBT
GaAs MESFET
InGaP HBT

support, contact

SiGe BiCMOS
 Si BiCMOS
 SiGe HBT

332-678-5570 or customerspryice@rfmd.

□ GaAs pHEMT □ GaN HEMT □ Si CMOS □ BiFET HBT ☑ Si BJT □ LDMOS

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Absolute Maximum Ratings

0		
Parameter	Rating	Unit
Operating Ambient Temperature[1]	-40 to +85	°C
Storage Temperature	-55 to +125	°C

[1] Frequency drift: 13MHz typical (either extreme)



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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RoHS (Restriction of Hazardous Substances): Compliant per EU Directive 2002/95/EC.

Parameter		Specification		11	O a statistica st
	Min.	Тур.	Max.	Unit	Condition
Overall					
Frequency Range		6525		MHz	
Tuning Voltage	0.5		4.5	V _{DC}	
Tuning Sensitivity		60		MHz/V	
Output Power	-3	0	2.5	dBm	
	-10	-5	0	dBm	1/2 frequency output
	-4			dBm	At V _T =0
Output Phase Noise		-70	-65	dBc/Hz	1kHz
		-96	-91	dBc/Hz	10kHz
		-116	-111	dBc/Hz	100 kHz
		-136	-131	dBc/Hz	1000kHz
		-156	-151	dBc/Hz	10000kHz
Second Harmonic		-20	-10	dBc	
Frequency Pulling		0.2	0.5	MHz p-p	At 12dBr, all phases
Tuning Port Capacitance		10		pF	
Modulation Bandwidth		1000		kHz	3dB BW
Frequency Pushing		3	5	MHz/V	
Power Supply					
Operating Voltage		5		V	
Supply Current		50		mA	





Package Drawing & Pin Outs

12.7mm x 12.7mm x 5.59mm (0.5in x 0.5in x 0.22in)

